

MANUFACTURING METHOD FOR SEMICONDUCTOR DEVICE

ABSTRACT

5 Embodiments of the present disclosure provide a method for manufacturing a semiconductor device, including: forming a sacrificial region on a surface of a substrate; forming a stacked structure on the sacrificial region, the stacked structure including a first semiconductor layer and a second semiconductor layer alternately stacked; removing the sacrificial region to form a cavity between the substrate and the
10 stacked structure; filling the cavity with an insulation layer; removing one of the first semiconductor layer and the second semiconductor layer; and forming a gate structure around the other of the first semiconductor layer and the second semiconductor layer.

Fig. 14A